

STS234XXXUXXX

TVS Diode array ESD suppressor



Product features

- Protects four I/O lines
- Low clamping voltage
- Low operating voltage
- Low capacitance
- Meets moisture sensitivity level (MSL) 3
- Molding compound flammability rating: UL 94V-0
- Termination finish: Tin

Applications

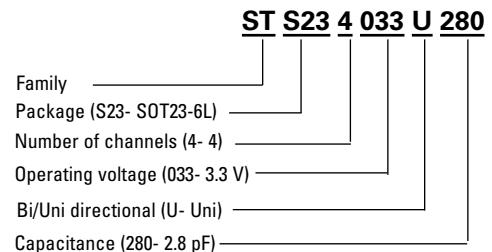
- USB power and data line protection
- Digital video interface (DVI)
- Notebook computers
- Video graphics cards
- Monitors and flat panel displays
- 10/100/1000 ethernet
- SIM ports
- ATM interfaces

Environmental compliance and general specifications

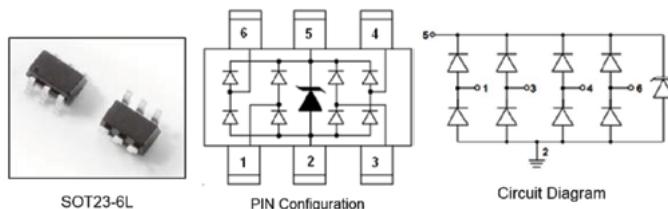
- IEC61000-4-2 (ESD)
 - Up to ± 30 kV (air)
 - Up to ± 30 kV (contact)
- IEC61000-4-5 (Lightning) Up to 24 A (8/20 μ s)



Ordering part number



Pin out/functional diagram



Absolute maximum ratings

(+25 °C, RH=45%-75%, unless otherwise noted)

Parameter	Symbol	Value					Unit
		STS234033U280	STS234050U160	STS234050UL30	STS234050UL65	STS234050U150	
Peak pulse power dissipation on 8/20 µs waveform	P _{pp}	500	300	100	100	500	W
Peak pulse current on 8/20 µs waveform	I _{pp}	-	-	8	-	-	A
ESD per IEC 61000-4-2 (Air)	V _{ESD}	+/-30	+/-30	+/-20	+/-30	+/-30	kV
ESD per IEC 61000-4-2 (Contact)		+/-30	+/-30	+/-20	+/-30	+/-30	
Lead soldering temperature	T _L	+260 (10 seconds)	°C				
Operating junction temperature range	T _J	-55 to +125	°C				
Storage temperature range	T _{STG}	-55 to +150	°C				

Electrical characteristics

(+25 °C)

STS234033U280

Parameter	Test condition	Minimum	Typical	Maximum	Symbol (Units)
Reverse working voltage	pin 5 to pin 2	-	-	3.3	V _{RWM} (V)
Reverse breakdown voltage	I _T = 1 mA pin 5 to pin 2	4.0	5.6	-	V _{BR} (V)
Reverse leakage current	V _{RWM} = 3.3 V pin 5 to pin 2	-	-	1	I _R (µA)
Forward voltage	I _T = 10 mA		0.8	1.2	V _F (V)
Clamping voltage	I _{pp} = 1 A, t _p = 8/20 µs	-	7	10	V _C (V)
	I _{pp} = 15 A, t _p = 8/20 µs	-	12	16	V _C (V)
	I _{pp} = 24 A, t _p = 8/20 µs	-	14	18	V _C (V)
Junction capacitance	V _{RWM} = 0 V, f = 1 MHz Any I/O pin to Ground	-	2.8	5	C _J (pF)
	V _{RWM} = 0 V, f = 1 MHz Between I/O pins	-	1.5	2.5	C _J (pF)

STS234050U160

Parameter	Test condition	Minimum	Typical	Maximum	Symbol (Units)
Reverse working voltage	-	-	-	5.0	V _{RWM} (V)
Reverse breakdown voltage	I _T = 1 mA	6.0	-	-	V _{BR} (V)
Reverse leakage current	V _{RWM} = 5 V pin 5 to pin 2	-	-	5	I _R (µA)
Forward voltage	I _T = 10 mA		1.2	-	V _F (V)
Clamping voltage	I _{pp} = 15 A, t _p = 8/20 µs	-	22	24.8	V _C (V)
Junction capacitance	V _{RWM} = 0 V, f = 1 MHz Any I/O pin to Ground	-	3	-	C _J (pF)
	V _{RWM} = 0 V, f = 1 MHz Between I/O pins	-	1.6	-	C _J (pF)

STS234050UL30

Parameter	Test condition	Minimum	Typical	Maximum	Symbol (Units)
Reverse working voltage	-	-	-	5.0	V_{RWM} (V)
Reverse breakdown voltage	$I_T = 1 \text{ mA}$	6.0	-	-	V_{BR} (V)
Reverse leakage current	$V_{RWM} = 5 \text{ V}$	-	-	1	I_R (μA)
Forward voltage	$I_T = 10 \text{ mA}$		0.8	1.0	V_F (V)
Clamping voltage	$I_{PP} = 1 \text{ A},$ $t_p = 8/20 \mu\text{s}$ $I_{PP} = 5 \text{ A},$ $t_p = 8/20 \mu\text{s}$	-	9.5	11	V_C (V)
Junction capacitance	$V_{RWM} = 0 \text{ V}, f = 1 \text{ MHz}$ Any I/O pin to Ground	-	0.65	0.8	C_J (pF)
	$V_{RWM} = 0 \text{ V}, f = 1 \text{ MHz}$ Between I/O pins	-	0.3	0.5	C_J (pF)

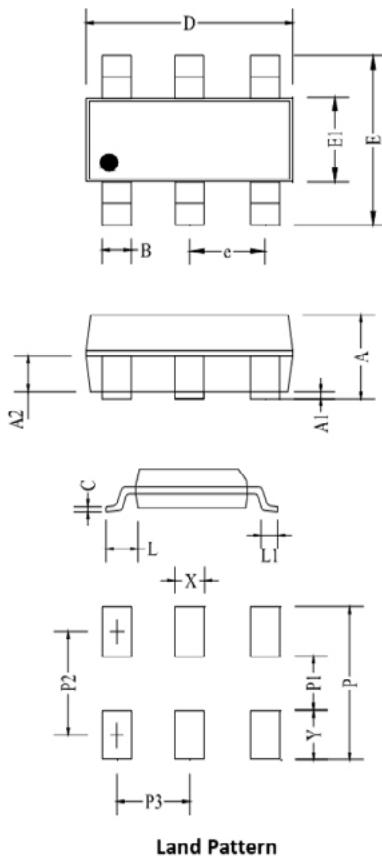
STS234050UL65

Parameter	Test condition	Minimum	Typical	Maximum	Symbol (Units)
Reverse working voltage	-	-	-	5.0	V_{RWM} (V)
Reverse breakdown voltage	$I_T = 1 \text{ mA}$	6.0	8.0	10.0	V_{BR} (V)
Reverse leakage current	$V_{RWM} = 5 \text{ V}$	-	0.01	0.1	I_R (μA)
Forward voltage	$I_T = 10 \text{ mA}$		0.8	1.2	V_F (V)
Clamping voltage	$I_{PP} = 1 \text{ A},$ $t_p = 8/20 \mu\text{s}$ $I_{PP} = 8 \text{ A},$ $t_p = 8/20 \mu\text{s}$	-	9.5	11	V_C (V)
Junction capacitance	$V_{RWM} = 0 \text{ V}, f = 1 \text{ MHz}$ Any I/O pin to Ground	-	1.2	1.5	C_J (pF)
	$V_{RWM} = 0 \text{ V}, f = 1 \text{ MHz}$ Between I/O pins	-	0.65	0.75	C_J (pF)

STS234050U150

Parameter	Test condition	Minimum	Typical	Maximum	Symbol (Units)
Reverse working voltage	pin 5 to pin 2	-	-	5.0	V_{RWM} (V)
Reverse breakdown voltage	$I_T = 1 \text{ mA}$ pin 5 to pin 2	0.6	-	9.0	V_{BR} (V)
Reverse leakage current	$V_{RWM} = 5 \text{ V}$ pin 5 to pin 2	-		0.5	I_R (μA)
Forward voltage	$I_T = 10 \text{ mA}$		-	1.2	V_F (V)
Clamping voltage	$I_{PP} = 1 \text{ A},$ $t_p = 8/20 \mu\text{s}$ $I_{PP} = 5 \text{ A},$ $t_p = 8/20 \mu\text{s}$ $I_{PP} = 24 \text{ A},$ $t_p = 8/20 \mu\text{s}$	-	9	10	V_C (V)
Junction capacitance	$V_{RWM} = 0 \text{ V}, f = 1 \text{ MHz}$ Any I/O pin to Ground	-	3	3.5	C_J (pF)
	$V_{RWM} = 0 \text{ V}, f = 1 \text{ MHz}$ Between I/O pins	-	1.5	2	C_J (pF)

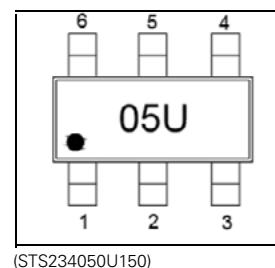
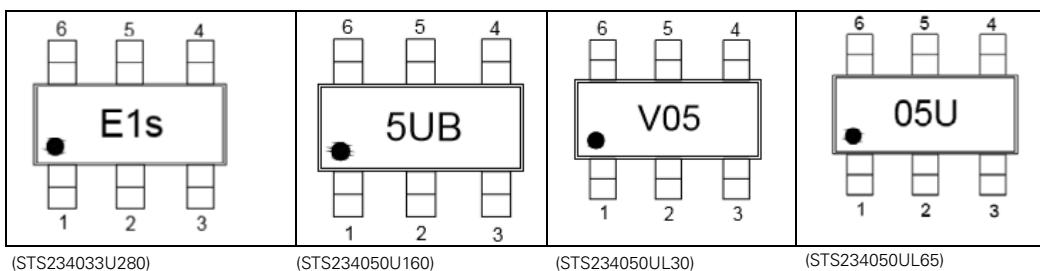
Mechanical parameters, pad layout- mm/inches



Dimension	Millimeters		Inches	
	Minimum	Maximum	Minimum	Maximum
A	0.90	1.45	0.035	0.057
A1	0.00	0.15	0.000	0.006
A2	0.45	0.65	0.017	0.026
B	0.35	0.50	0.010	0.020
C	0.08	0.20	0.003	0.007
D	2.80	3.00	0.110	0.122
e	0.69	1.02	0.032	0.043
E1	1.50	1.75	0.060	0.069
E	2.80 BSC		0.110 BSC	
L1	0.35	0.60	0.013	0.024
L	0.60		0.024	
X	0.60		0.024	
Y	1.10		0.043	
P	3.60		0.141	
P1	1.40		0.055	
P2	2.50		0.098	
P3	0.95		0.037	

Land Pattern

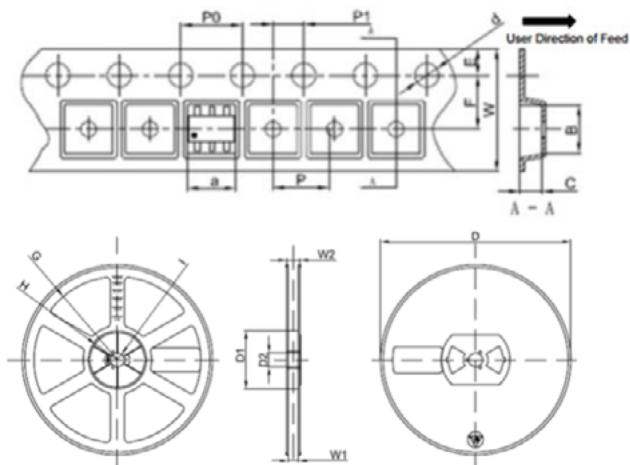
Part marking



Packaging information mm/inches

Drawing not to scale.

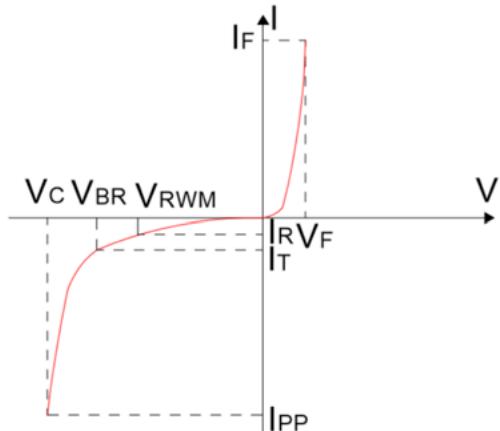
Supplied in tape and reel packaging, 3,000 parts per 7" diameter reel (EIA-481 compliant)



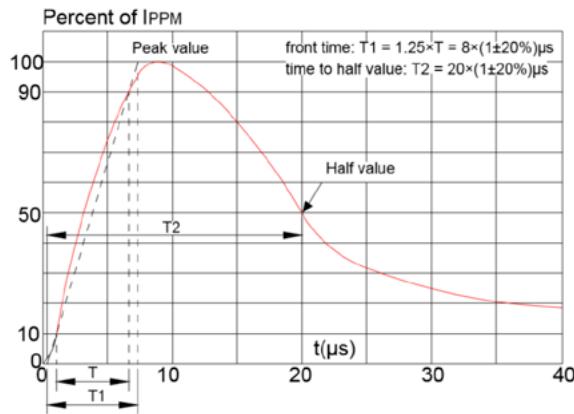
Symbol	Millimeter	Inches
	Typ.	Typ.
a	3.17	0.125
B	3.23	0.127
C	1.37	0.054
d	Φ 1.55	Φ 0.061
E	1.75	0.069
F	3.50	0.138
P0	4.00	0.157
P	4.00	0.157
P1	2.00	0.079
W	8.00	0.315
D	Φ 180	Φ 7.087
D1	60.00	2.632
D2	13.00	0.512
G	R78.00	R3.071
H	R25.60	R1.008
I	R6.50	R0.256
W1	9.50	0.374
W2	13.10	0.516

Ratings and V-I characteristic curves (+25 °C unless otherwise noted)

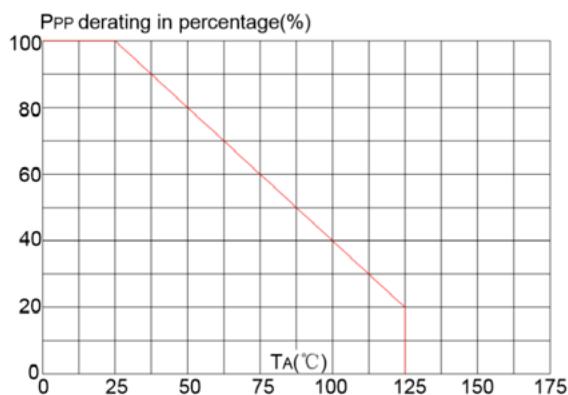
V-I curve characteristics (Uni-directional)



Pulse waveform (8/20 μ s)



Pulse derating curve



ESD waveform

